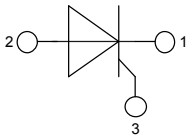
High Efficiency Thyristor

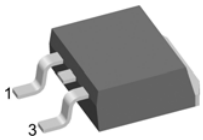
Single Thyristor

V_{RRM} = 1200 V
$I_{T(AV)M}$ = 30 A
$I_{T(RMS)}$ = 47 A

Part number

CLA 30 E 1200 PC





Backside: anode

Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

Applications:

- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package:

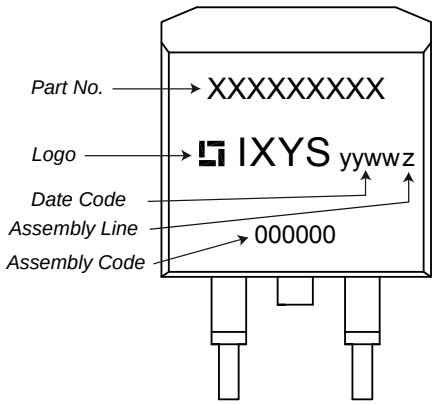
- Housing: TO-263 (D2Pak)
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1300	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1200	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 1200 V	T_{VJ} = 25°C			10	µA
		$V_{R/D}$ = 1200 V	T_{VJ} = 125°C			2	mA
V_T	*forward voltage drop*	I_T = 30 A	T_{VJ} = 25°C			1.30	V
		I_T = 60 A				1.59	V
		I_T = 30 A	T_{VJ} = 125°C			1.27	V
		I_T = 60 A				1.65	V
$I_{T(AV)M}$	*average forward current*	T_C = 115°C	T_{VJ} = 150°C			30	A
$I_{T(RMS)}$	*RMS forward current*	180° sine				47	A
V_{T0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.86	V
r_T	*slope resistance* }					13.2	mΩ
R_{thJC}	*thermal resistance junction to case*					0.65	K/W
T_{VJ}	*virtual junction temperature*			-40		150	°C
P_{tot}	*total power dissipation*		T_C = 25°C			190	W
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0.5	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			300	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			325	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			255	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			275	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			450	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			440	A²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			325	A²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			315	A²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		13		pF

Symbol	Definition	Conditions	Ratings min.	typ.	max.	Unit
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 150 °C repetitive, I_T = 40 A			150	A/µs
		f = 50 Hz; t_P = 200 µs				
		I = 0.3 A; di /dt = 0.3 A/µs				
		V_D = ⅔ V_{DRM} non-repetitive, I_T = 30 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V_D = ⅔ V_{DRM} T_{VJ} = 150 °C			500	V/µs
		R_{GK} = ∞; method 1 (linear voltage rise)				
V_{GT}	*gate trigger voltage*	V_D = 6 V T_{VJ} = 25 °C			1.3	V
		T_{VJ} = -40 °C			1.6	V
I_{GT}	*gate trigger current*	V_D = 6 V T_{VJ} = 25 °C			30	mA
		T_{VJ} = -40 °C			50	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM} T_{VJ} = 150 °C			0.2	V
I_{GD}	*gate non-trigger current*				1	mA
I_L	*latching current*	t_p = 10 µs T_{VJ} = 25 °C			90	mA
		I = 0.3 A; di /dt = 0.3 A/µs				
I_H	*holding current*	V_D = 6 V R_{GK} = ∞ T_{VJ} = 25 °C			60	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM} T_{VJ} = 25 °C			2	µs
		I = 0.3 A; di /dt = 0.3 A/µs				
t_q	*turn-off time*	V_R = 100 V; I_T = 30 A T_{VJ} = 150 °C		150		µs
		V_D = ⅔ V_{DRM}; t_p = 200 µs				
		di/dt = 10 A/µs; dv/dt = 20 V/µs				

Symbol	Definition	Conditions	Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal			35	A
R_{thCH}	*thermal resistance case to heatsink*			0.25		K/W
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g
F_C	*mounting force with clip*		20		60	N

Product Marking



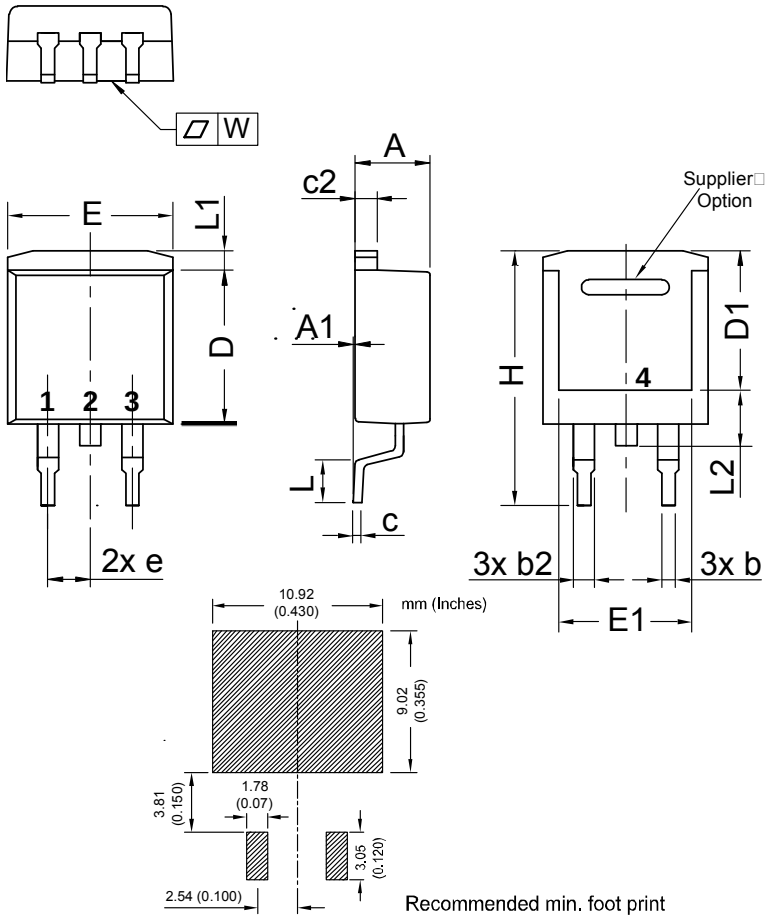
Part number

C = Thyristor (SCR)
L = High Efficiency Thyristor
A = (up to 1200 V)
30 = Current Rating [A]
E = Single Part
1200 = Reverse Voltage [V]
PC = TO-263AB (D2Pak) (2)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	CLA 30 E 1200 PC	CLA30E1200PC	Tape & Reel	800	508235

Similar Part	Package	Voltage class
CLA30E1200PB	TO-220AB (3)	1200
CLA30E1200HB	TO-247AD (3)	1200
CS22-12io1M	TO-220ABFP (3)	1200
CS22-08io1M	TO-220ABFP (3)	800
CMA30E1600PN	TO-220ABFP (3)	1600
CMA30E1600PB	TO-220AB (3)	1600

Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.029
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
E	9.65	10.41	0.380	0.410
E1	6.22	8.20	0.245	0.323
e	2,54 BSC		0,100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
L2	1.02	1.52	0.040	0.060
W	typ. 0.02	0.040	typ. 0.0008	0.0016

All dimensions conform with and/or are within JEDEC standard.

Recommended min. foot print

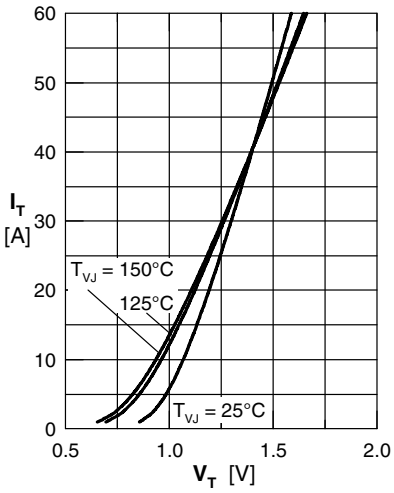


Fig. 1 Forward characteristics

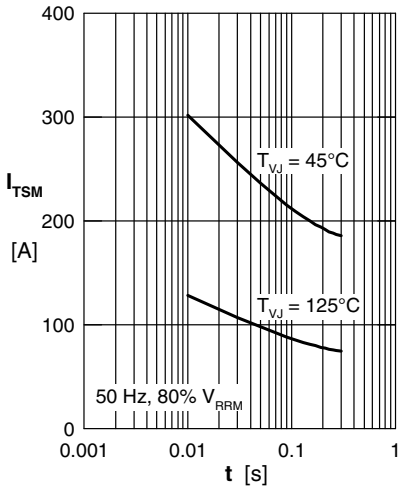


Fig. 2 Surge overload current
I_{TSM}: crest value, t: duration

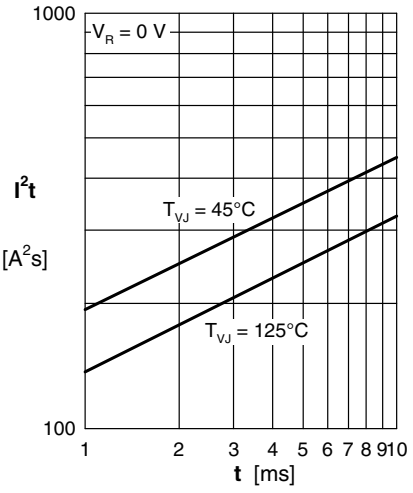


Fig. 3 I^2t versus time (1-10 s)

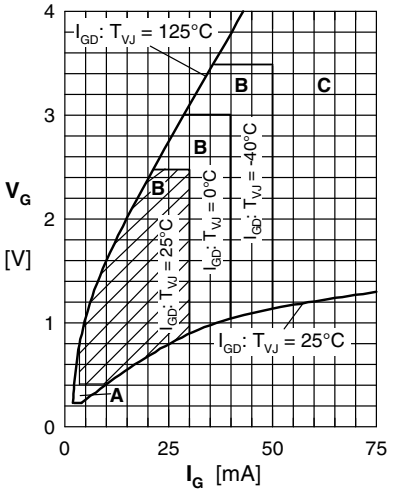


Fig. 4 Gate voltage & gate current
Triggering: A = no; B = possible; C = safe

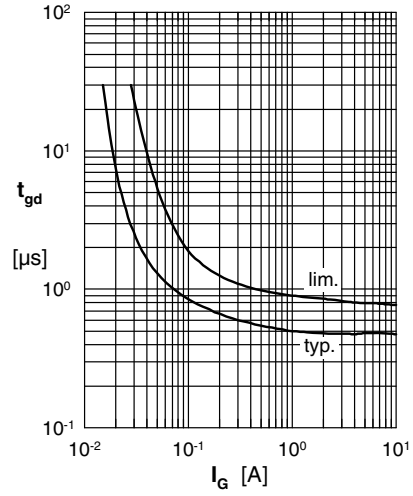


Fig. 5 Gate controlled delay time t_{gd}

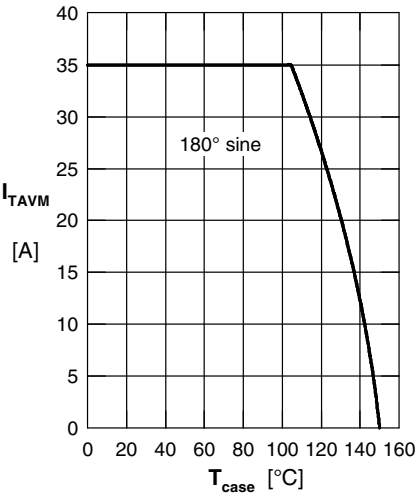


Fig. 6 Max. forward current at case temperature

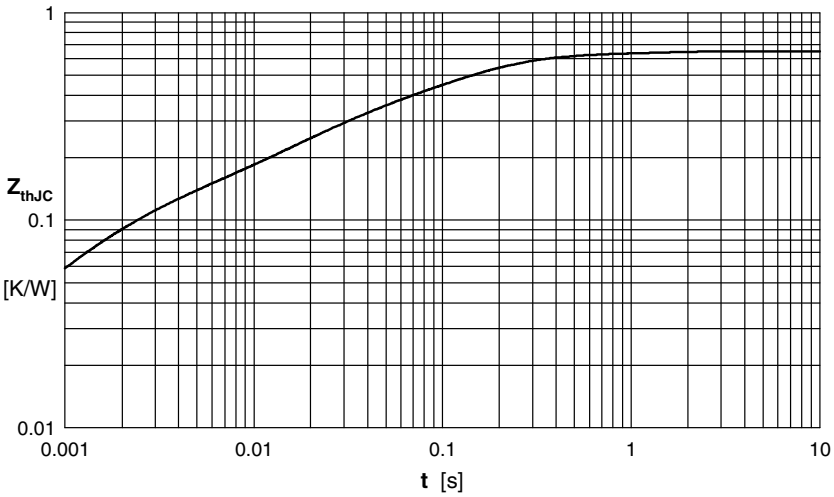


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.024	0.0007
2	0.069	0.0018
3	0.148	0.018
4	0.053	0.12
5	0.356	0.76